Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1516	(system or apparatus) with (spin near coating)	US-PGPUB; USPAT	OR	ON	2006/02/01 07:44
L2	71	1 and (pressure with (detector or sensor))	US-PGPUB; USPAT	OR	ON	2006/02/01 07:54
L3	35	2 and @ad<"20021015"	US-PGPUB; USPAT	OR	ON	2006/02/01 07:54
L4	792	(spin near coating) and (pressure with (detector or sensor))	US-PGPUB; USPAT	OR	ON	2006/02/01 07:54
L5	1070	(spin near coating) and (pressure with (detector or sensor or gauge))	US-PGPUB; USPAT	OR	ON	2006/02/01 07:54
L6	636	5 and @ad<"20021015"	US-PGPUB; USPAT	OR	ON	2006/02/01 07:55
L7	601	6 not 3	US-PGPUB; USPAT	OR	ON	2006/02/01 07:55

US-PAT-NO:

6098650

DOCUMENT-IDENTIFIER: US 6098650 A

TITLE:

Pressure sensing apparatus for regulating the

transportation of a liquid

	<b>KWIC</b>	
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### Brief Summary Text - BSTX (8):

Currently local planarization on the substrate surface is accomplished using spin-on glass (SOG). The SOG process includes two steps: coating and curing. SOG uses a solution that includes a dielectric material in a solvent, for <u>spin</u> <u>coating</u> onto the substrate. The dielectric material in solution fills the concave structures on the substrate to obtain a local planarization. The coating is followed by curing, which dries the residual solution of SOG out of the substrate in a thermal process that bakes the substrate, solidifying the SOG solution into a crystal structure such as SiO.sub.2.

### Brief Summary Text - BSTX (13):

It is another objective of the present invention to provide a <u>pressure</u> sensing apparatus including a <u>sensor</u> for detecting whether or not the <u>pressure</u> of the chemical solution is kept at a relative constant level, thus ensuring that the flow rate is precisely regulated.

# Detailed Description Text - DETX (12):

The apparatus uses a <u>sensor</u> for detecting the internal <u>pressure</u> so that the internal <u>pressure</u> of the container 52 can be kept in a relatively constant range.

US-PAT-NO: 6056998

DOCUMENT-IDENTIFIER: US 6056998 A

TITLE: Coating apparatus and coating method

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## Brief Summary Text - BSTX (4):

At present, mostly used as the method for coating the resist solution over a wafer is a **spin-coating** method. In the **spin coating** method, a resist solution is pumped up from a tank, filtrated by a filter, and spurted out from a nozzle toward the wafer W by way of an operate valve. Since the wafer W is spin-rotated while being held by a spin chuck, the resist solution is spread swiftly over the entire wafer surface by centrifugal force, thereby forming a resist film having a uniform thickness.

### Brief Summary Text - BSTX (10):

The present inventors formed films on silicon wafers by applying a coating solution 85a containing a surfactant by use of the apparatus shown in FIG. 14 (Comparative Example) and by use of an apparatus shown in FIG. 15 (Example). Comparison was made between the films of Comparative Example and those of Example. The coating solution supply route of the apparatus (Comparative Example) has a tank 201, an upstream pump 202a, a filter 203, a downstream pump 202b, an operate valve 204, and a nozzle 205 which are arranged in the order mentioned from the upstream. The coating solution supply route of the apparatus (Example) has a tank 71A, a filter 73A, a downstream pump 75A, an operate valve 74, and a nozzle 86A, which are arranged in the order mentioned from the upstream. The apparatus (Example) is further equipped with a pressure-difference detector 197 and a controller 198. The pressure-difference detector 197 detects difference in pressure between a primary side (upstream side) and a secondary side (downstream side) of the filter 73A. The controller controls the downstream pump 75A on the basis of the pressure-difference detection signal detected from the pressure-difference detector 197.

# Brief Summary Text - BSTX (12):

On the other side, in the apparatus of Example, the <u>pressure</u> difference between the primary side and the secondary side of the filter 203 can be suppressed by the controller 198 in combination with the <u>pressure</u>-difference <u>detector</u> 197. It is therefore possible for the captured materials such as

particles to stay in the filter at the time the solution is spurted out. Furthermore, since only one pump 75A is employed, the apparatus can be reduced in size.